

12V PNP SILICON LOW SATURATION SWITCHING TRANSISTOR AND SCHOTTKY DIODE

SUMMARY

Transistor: $V_{CE0} = -12V$, $I_C = -1.25A$

Schottky Diode: $V_R = 40V$; $I_C = 0.5A$

DESCRIPTION

A PNP transistor and a Schottky Barrier diode contained in a single 6 leaded SOT23 package.

FEATURES

- Low Saturation Transistor
- High Gain - 300 minimum
- Low V_F , fast switching Schottky

APPLICATIONS

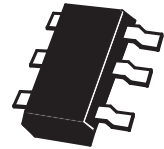
- Mobile telecomms, PCMCIA & SCSI
- DC-DC Conversion

ORDERING INFORMATION

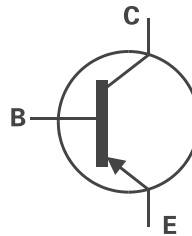
DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXTS1000E6TA	7	8mm embossed	3000 units
ZXTS1000E6TC	13	8mm embossed	10000 units

DEVICE MARKING

1000



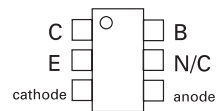
SOT23-6



Cathode



Anode



Top View

ZXTS1000E6

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Transistor			
Collector-Base Voltage	V_{CBO}	-12	V
Collector-Emitter Voltage	V_{CEO}	-12	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-1.25	A
Schottky Diode			
Continuous Reverse Voltage	V_R	40	V
Forward Current	I_F	0.5	A
Non Repetitive Forward Current $t \leq 100\mu s$	I_{FSM}	6.75	A
$t \leq 10ms$		3	A
Package			
Power Dissipation at $T_{amb}=25^\circ C$ single die "on" both die "on"	P_D	0.725	W
		0.885	W
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ C$
Junction Temperature	T_j	125	$^\circ C$

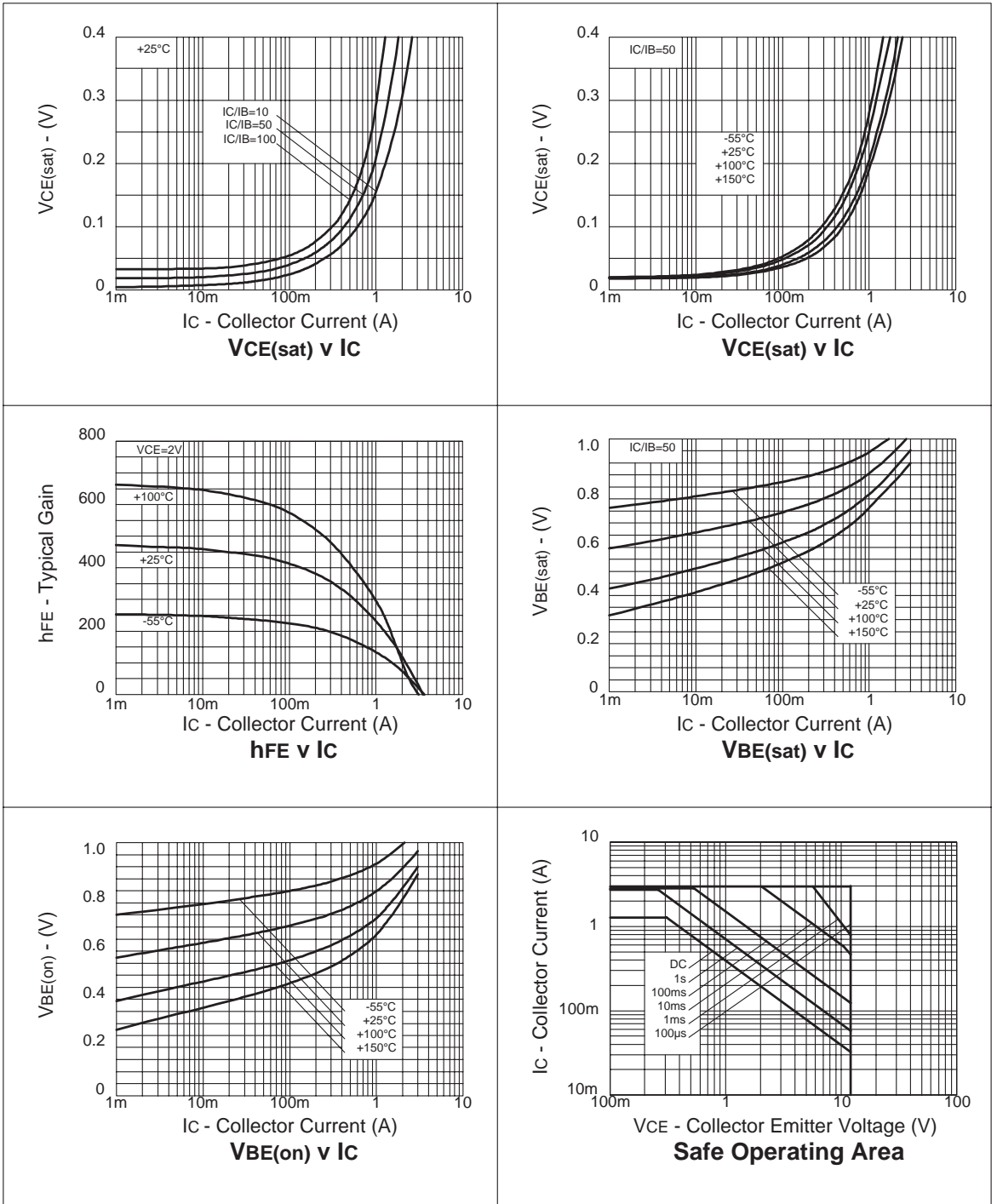
THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a) single die "on"	$R_{\theta JA}$	138	$^\circ C/W$
both die "on"	$R_{\theta JA}$	113	$^\circ C/W$

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

TRANSISTOR TYPICAL CHARACTERISTICS



ZXTS1000E6

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

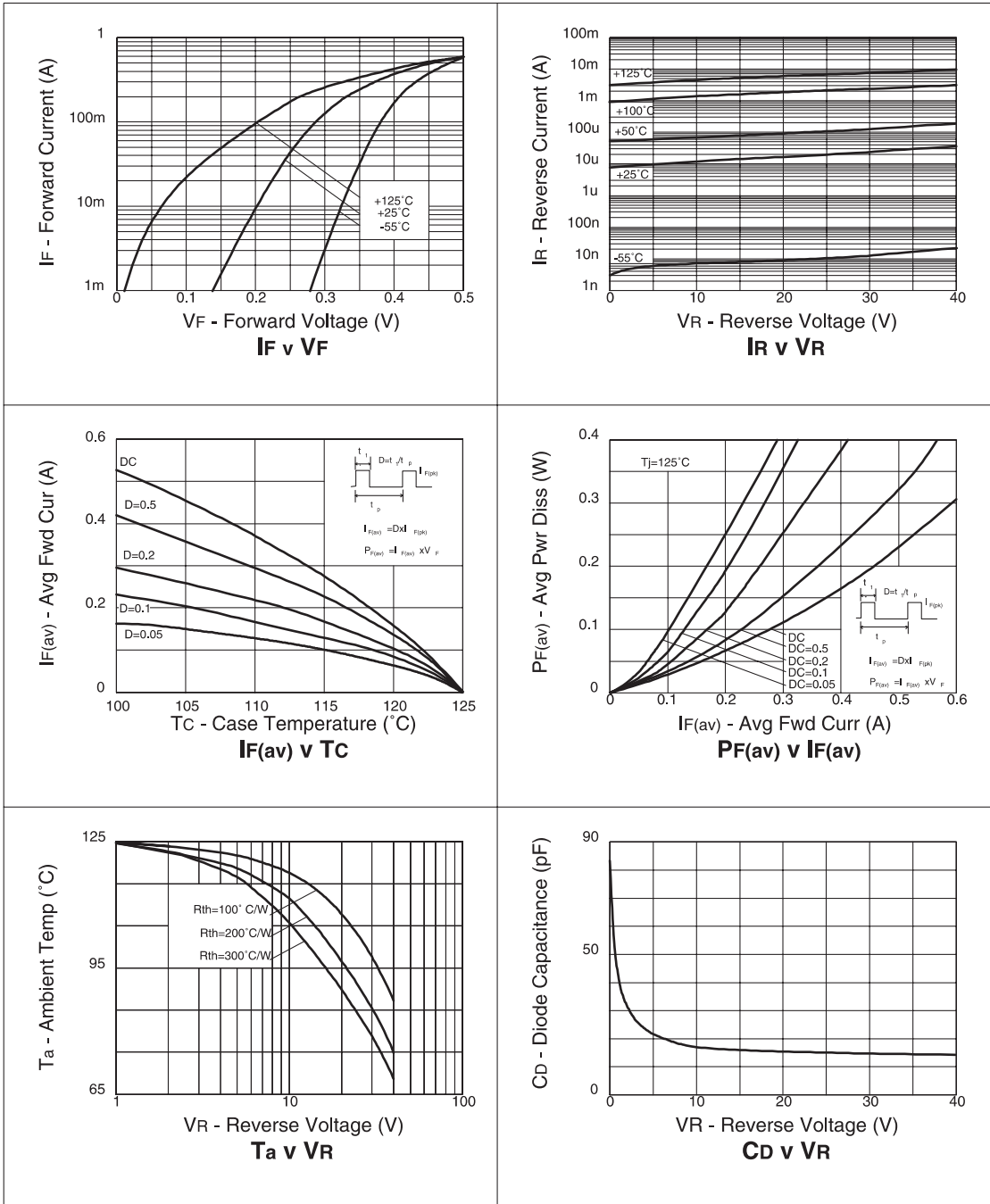
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
TRANSISTOR ELECTRICAL CHARACTERISTICS						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-12			V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-12			V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-10	nA	$V_{CB} = -10\text{V}$
Emitter Cut-Off Current	I_{EBO}			-10	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			-10	nA	$V_{CES} = -10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-25 -55 -110 -160 -185	-40 -100 -175 -215 -240	mV mV mV mV mV	$I_C = -0.1\text{A}, I_B = -10\text{mA}^*$ $I_C = -0.25\text{A}, I_B = -10\text{mA}^*$ $I_C = -0.5\text{A}, I_B = -10\text{mA}^*$ $I_C = -1\text{A}, I_B = -50\text{mA}^*$ $I_C = -1.25\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-990	-1100	mV	$I_C = -1.25\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-850	-1000	mV	$I_C = -1.25\text{A}, V_{CE} = 2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 300 200 125 75 30	490 450 340 250 140 80			$I_C = -10\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -0.1\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -0.5\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -1.25\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -2\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -3\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	f_T		220		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		15		pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		50		ns	$V_{CC} = -10\text{V}, I_C = -1\text{A}$ $I_{B1} = I_{B2} = -100\text{mA}$
Turn-Off Time	$t_{(off)}$		135		ns	

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS

Reverse Breakdown Voltage	$V_{(BR)R}$	40	60		V	$I_R = 200\mu\text{A}$
Forward Voltage	V_F		270 300 370 425 550 640 810	300 350 460 550 670 780 1050	mV mV mV mV mV mV mV	$I_F = 50\text{mA}^*$ $I_F = 100\text{mA}^*$ $I_F = 250\text{mA}^*$ $I_F = 500\text{mA}^*$ $I_F = 750\text{mA}^*$ $I_F = 1000\text{mA}^*$ $I_F = 1500\text{mA}^*$
Reverse Current	I_R		15	40	μA	$V_R = 30\text{V}$
Diode Capacitance	C_D		20		pF	$f = 1\text{MHz}, V_R = 30\text{V}$
Reverse Recovery Time	t_{rr}		10		ns	switched from $I_F = 500\text{mA}$ to $I_R = 500\text{mA}$ Measured at $I_R = 50\text{mA}$

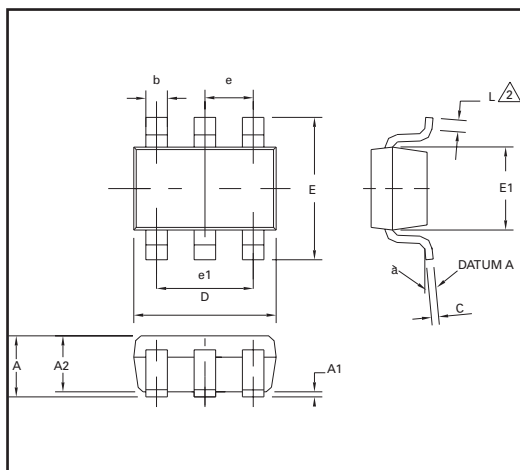
*Measured under pulsed conditions.

DIODE TYPICAL CHARACTERISTICS

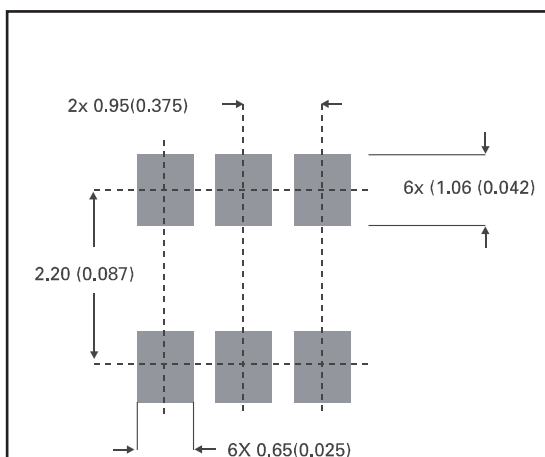


ZXTS1000E6

PACKAGE DIMENSIONS



PAD LAYOUT DETAILS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	0.90	1.45	0.35	0.057
A1	0.00	0.15	0	0.006
A2	0.90	1.30	0.035	0.051
b	0.35	0.50	0.014	0.019
C	0.09	0.20	0.0035	0.008
D	2.80	3.00	0.110	0.118
E	2.60	3.00	0.102	0.118
E1	1.50	1.75	0.059	0.069
L	0.10	0.60	0.004	0.002
e	0.95 REF		0.037 REF	
e1	1.90 REF		0.074 REF	
L	0°	10°	0°	10°



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